



General Description

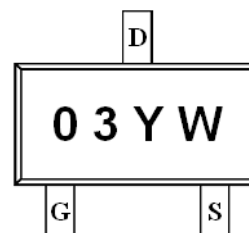
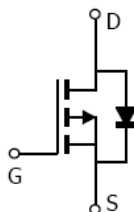
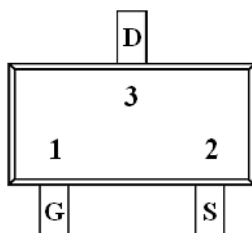
AFP1303, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -20V/-1.8A, $R_{DS(ON)} = 600 \text{ m}\Omega @ V_{GS} = -4.5\text{V}$
- -20V/-1.5A, $R_{DS(ON)} = 800 \text{ m}\Omega @ V_{GS} = -2.5\text{V}$
- -20V/-1.2A, $R_{DS(ON)} = 1300 \text{ m}\Omega @ V_{GS} = -1.8\text{V}$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-323 package design

Pin Description (SOT-323)



Application

- Net Working System
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Paggers

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP1303S32RG	03YW	SOT-323	Tape & Reel	3000 EA

- ※ 03 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP1303S32RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-1.0
		T _A =70°C	-0.6
Pulsed Drain Current	I _{DM}	-6	A
Continuous Source Current(Diode Conduction)	I _S	-1	A
Power Dissipation	P _D	T _A =25°C	0.35
		T _A =70°C	0.22
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

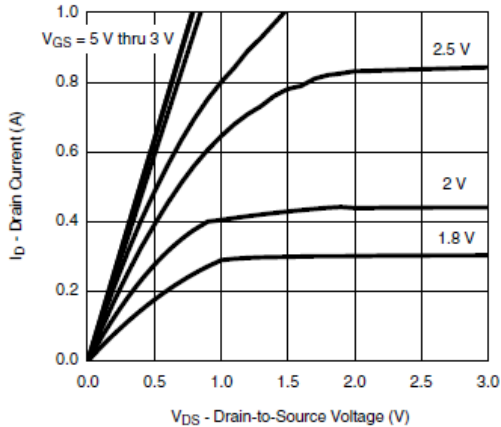
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

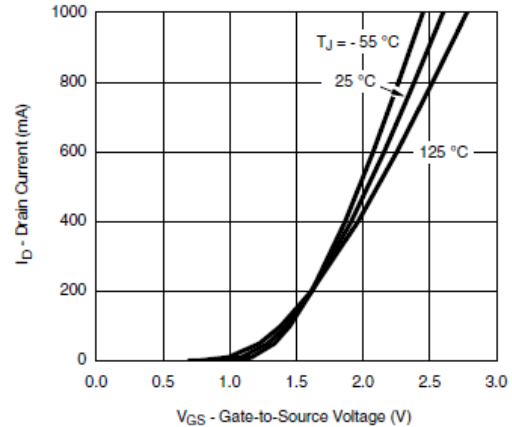
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.4		-1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	uA
		V _{DS} =-20V, V _{GS} =0V T _J =85°C			-5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =4.5V	0.7			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-1.8A		500	600	mΩ
		V _{GS} =-2.5V, I _D =-1.5A		700	800	
		V _{GS} =-1.8V, I _D =-1.2A		1000	1300	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-0.4A		1		S
Diode Forward Voltage	V _{SD}	I _S =-0.15A, V _{GS} =0V		0.65	1.2	V
Dynamic						
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V f=1MHz		70	100	pF
Output Capacitance	C _{oss}			20		
Reverse Transfer Capacitance	C _{rss}			10		
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-4.5V I _D ≡-0.25A		1.0	1.3	nC
Gate-Source Charge	Q _{gs}			0.1		
Gate-Drain Charge	Q _{gd}			0.3		
Turn-On Time	t _{d(on)}	V _{DD} =-10V, R _L =30Ω I _D ≡-0.2A, V _{GEN} =-4.5V R _G =10Ω		10	15	ns
	t _r			10	15	
Turn-Off Time	t _{d(off)}			40	60	
	t _f			30	50	



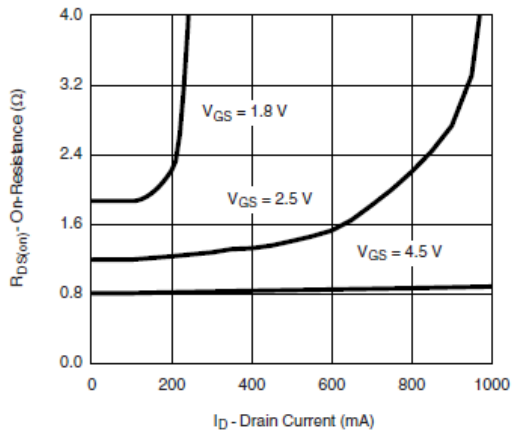
Typical Characteristics



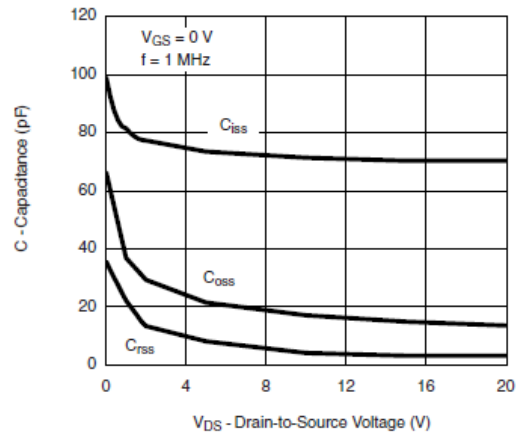
Output Characteristics



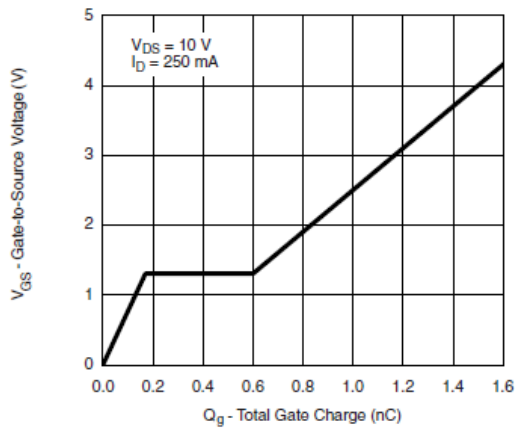
Transfer Characteristics



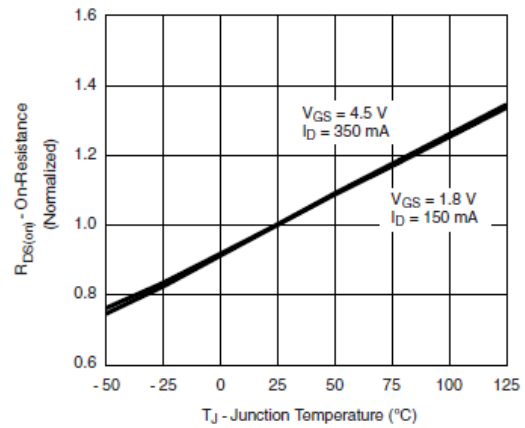
On-Resistance vs. Drain Current



Capacitance



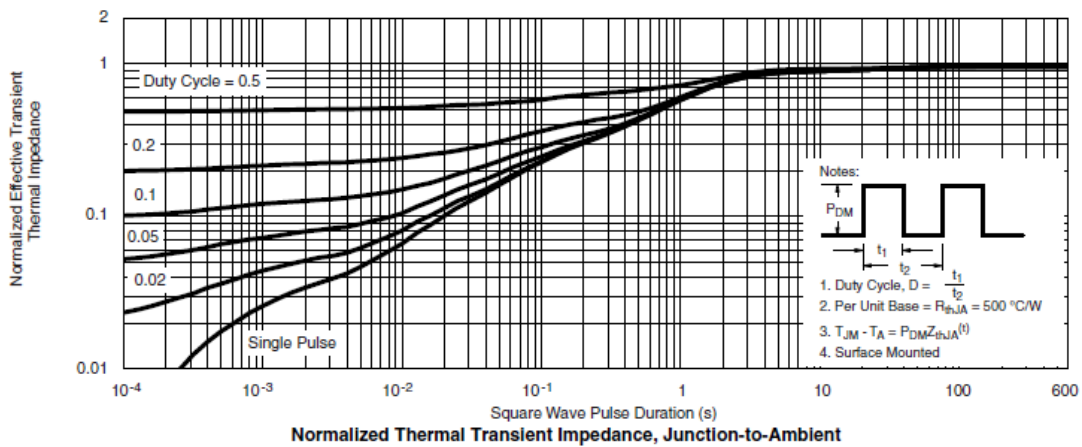
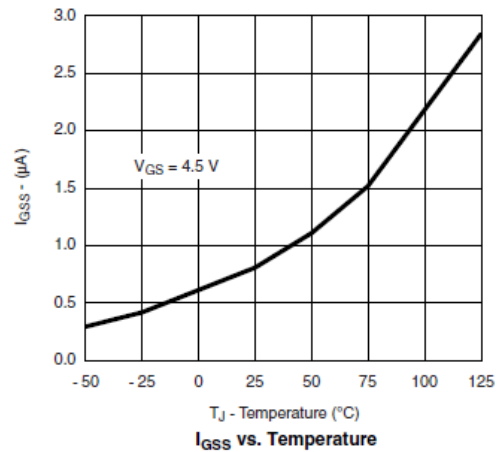
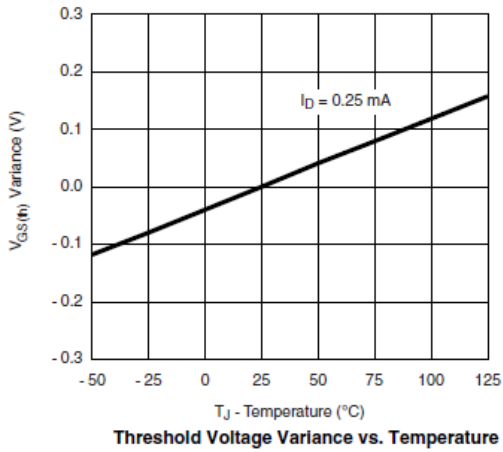
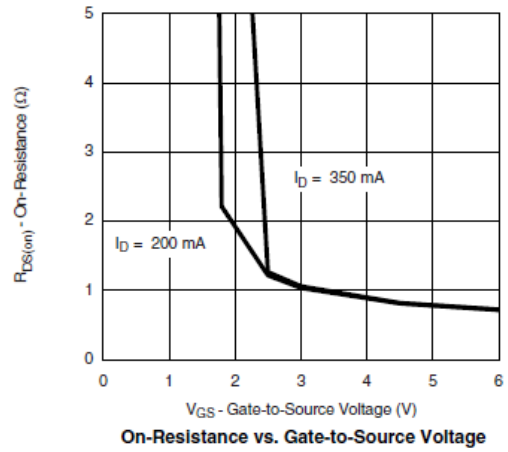
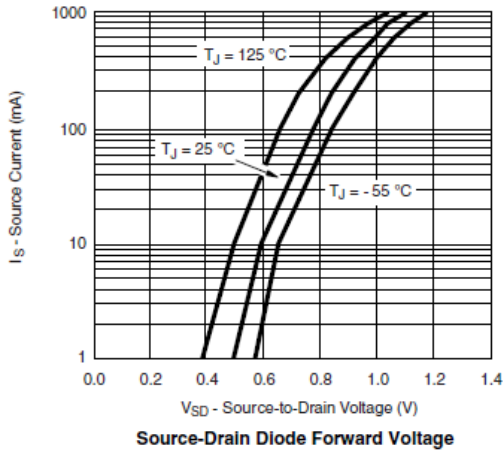
Gate Charge



On-Resistance vs. Junction Temperature



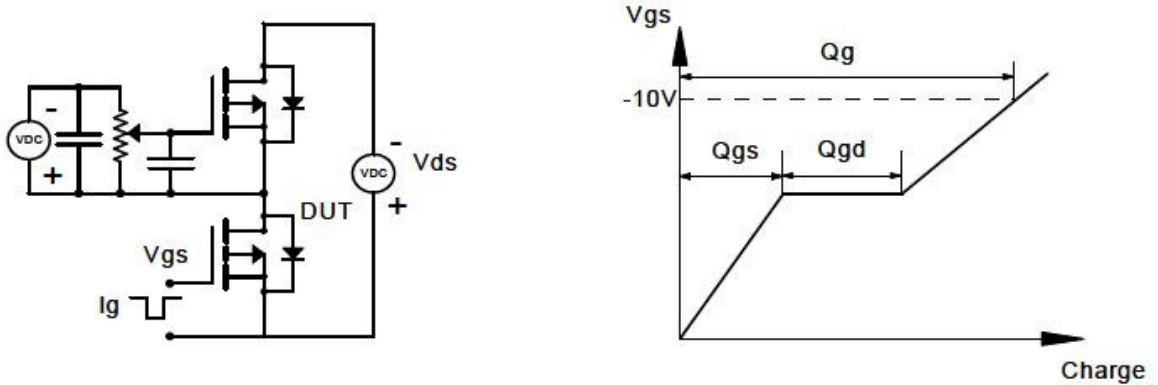
Typical Characteristics



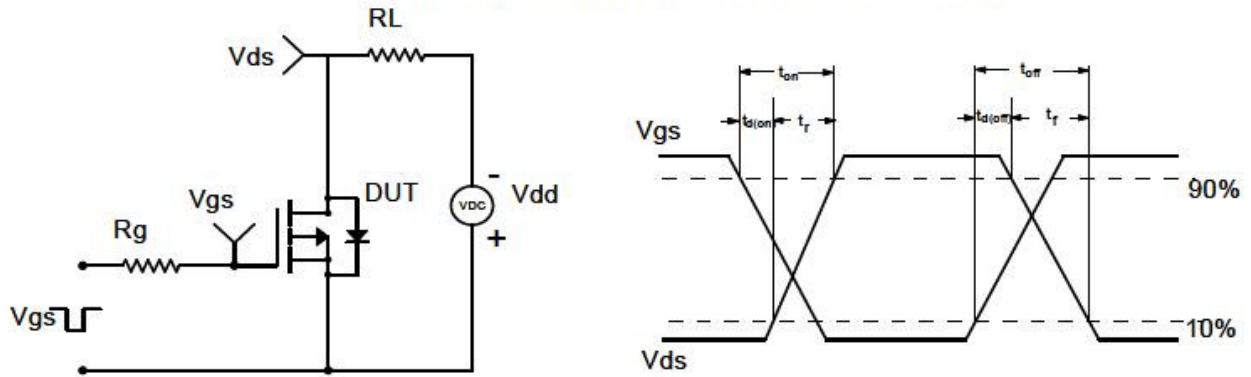


Typical Characteristics

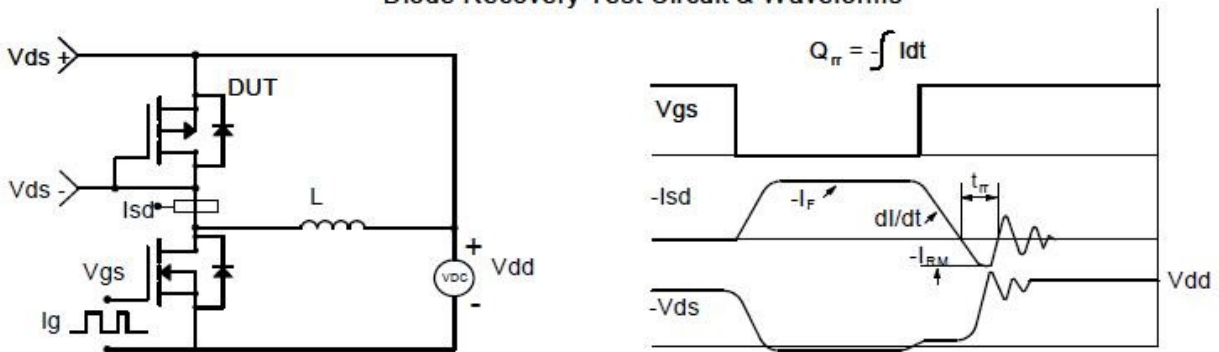
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

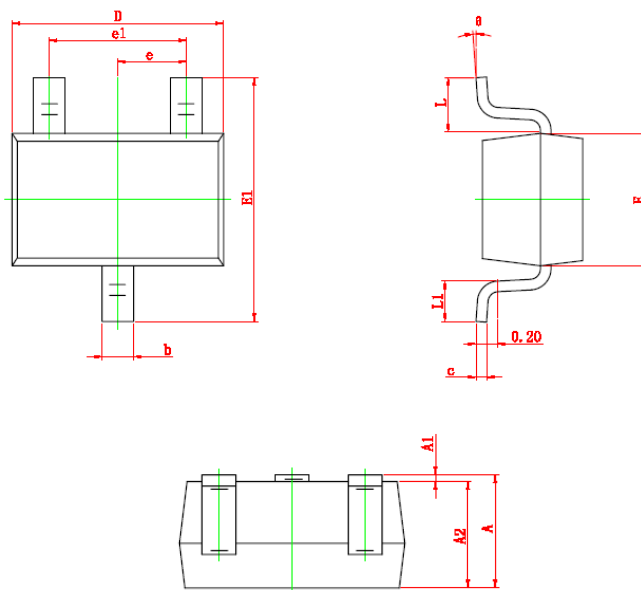


Diode Recovery Test Circuit & Waveforms





Package Information (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

©2010 Alfa-MOS Technology Corp.
 2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)
 Tel : 886 2) 2651 3928
 Fax : 886 2) 2786 8483
 ©http://www.alfa-mos.com